

KATHMANDU UNIVERSITY
End Semester Examination
July/August 2024

Level : B.E.
Year : II
Time : 2 hrs. 30mins.

0 7 AUG 2024

Course : EEG 211
Semester : I
F. M. : 40

SECTION "B"
[5 Q. × 8 = 40 marks]

Attempt *ANY FIVE* questions. Assume suitable data, if necessary. Symbol has their usual meaning.

1.
 - a. Discuss the characteristics curve of rectifier diode. Also, derive the expression of efficiency calculation for center tap full wave rectifier circuit. [2+2=4]
 - b. What is a clipper circuit? Draw and explain the output waveform for the circuit provided in Fig. 1. [2+2=4].

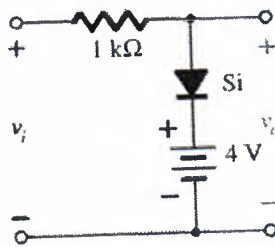
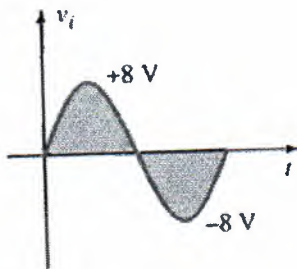


Fig. 1

2.
 - a. Derive the expressions of gains for, [2+2=4]
 - i. Non-inverting amplifier.
 - ii. Differential input amplifier.
 - b. In the reference Fig. 2, determine the output voltage (V_o) for the given op-amp circuit. [4]

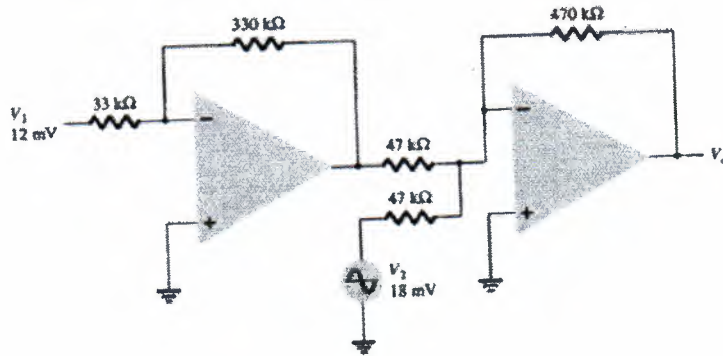


Fig. 2

P.T.O.

3.

- a. For Fig. 3, $I_{CQ} = \frac{1}{2} I_{Sat}$, $I_{Sat} = 8mA$, $V_C = 18V$, $\beta = 100$. Determine R_C , R_E , and R_B , & V_{CEQ} for Fig.3. [4]

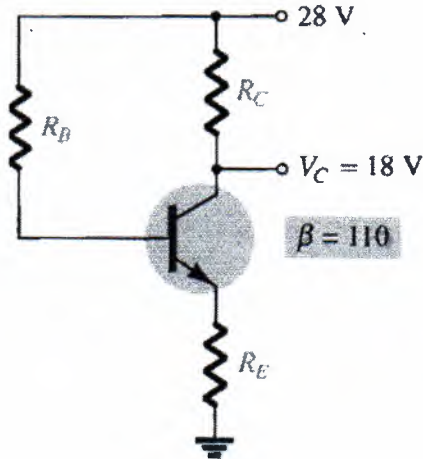


Fig. 3

- b. For a single stage amplifier shown in Fig 4, derive the expression for the following parameters and estimate the values: [3+1=4]
- Determine r_e
 - Input impedance (Z_i)
 - Output impedance (Z_o)
 - Voltage Gain (A_V)

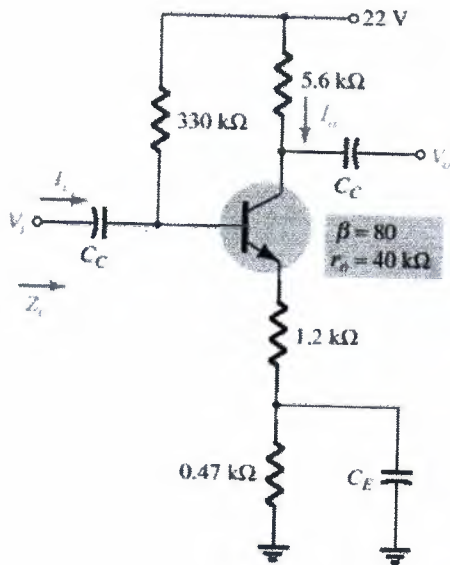


Fig. 4

4.

- Derive the efficiency of Class A type power amplifier. How the efficiency of Class A amplifier can be increased? Discuss it with transformer coupled concept. [2+1+1=4]
- For a class B amplifier providing a 20-V peak signal to a 16-ohm load (speaker) and a power supply of $V_{CC} = 30V$, determine the input power, output power, and circuit efficiency. [4]

5.

- a. Explain the construction and working principle of n-channel E-MOSFET with its drain characteristics.
- b. Determine the required values of drain current (I_D) and V_{DS} for a given circuit in Fig.5

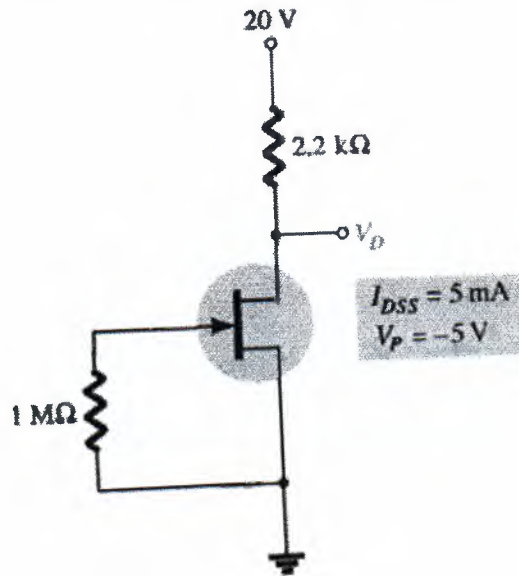


Fig. 5

6.

- a. Using the information provided in Fig. 6, Determine I_C , V_E , V_B and R_1 .

[4]

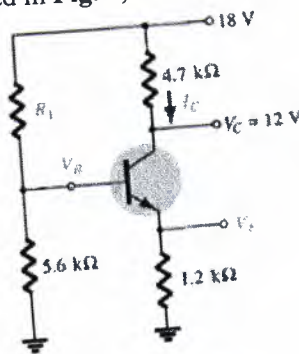


Fig. 6

- b. Discuss the design procedure of low frequency amplifier using BJT.

[4]

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Marks Scored:

Level : B.E.

Year : II

Exam Roll No. :

Time: 30 mins.

Course : EEG 211

Semester : I

F. M. : 10

Registration No.:

Date : 02 AUG 2024

SECTION "A"

[20Q. \times 0.5 = 10 marks]

Choose and encircle the most appropriate option from each set of choices. Symbols have their usual meaning.

- P-N junction diode is used for _____.
 regulator IC rectifier circuit
 everywhere in circuit amplifier
- Addition of pentavalent impurity to a pure semiconductor creates many _____.
 free electrons valence electrons free holes bound holes
- Which of the following parameter will be very high in the CB configuration of a BJT?
 current gain voltage gain input resistance output resistance
- The value of R_s required for an n-channel JFET with $V_p = -10 V$, $I_{DSS} = 40 mA$, and $V_{GSQ} = -5V$ is _____.
 500 Ω 750 Ω 1155 Ω 1500 Ω
- The value of ripple factor in full wave rectifier circuit is nearly equal to _____.
 0.41 0.48 0.82 1.21
- Which of the following is NOT a necessary component in a clamper circuit?
 Resistor Diode DC supply Capacitor
- The input impedance of a transistor is _____.
 very high high almost zero low
- The current amplification factor in CC configuration is _____.
 α $\beta + 1$ β γ
- In BJT, the equation $I_C = \alpha I_E + \frac{\quad}{\quad}$.
 I_B I_{CBO} I_{CEO} βI_B
- In a transistor, $I_C = 100 mA$ and $I_E = 100.2 mA$. The value of β is _____.
 about 1 50 100 200
- As the temperature of a transistor goes up, the base-emitter resistance _____.
 decrease increase remains constant fluctuates

